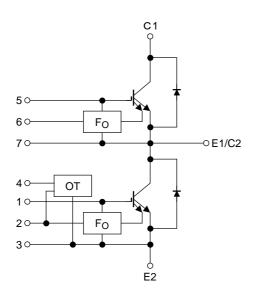
TOSHIBA IGBT Module Silicon N Channel IGBT

# MG400J2YS60A(600V/400A 2in1)

High Power Switching Applications Motor Control Applications

- Integrates a complete half bridge power circuit and fault-signal output circuit in one package. (short circuit and over temperature)
- The electrodes are isolated from case.
- Low thermal resistance
- VCE (sat) = 1.8 V (typ.)

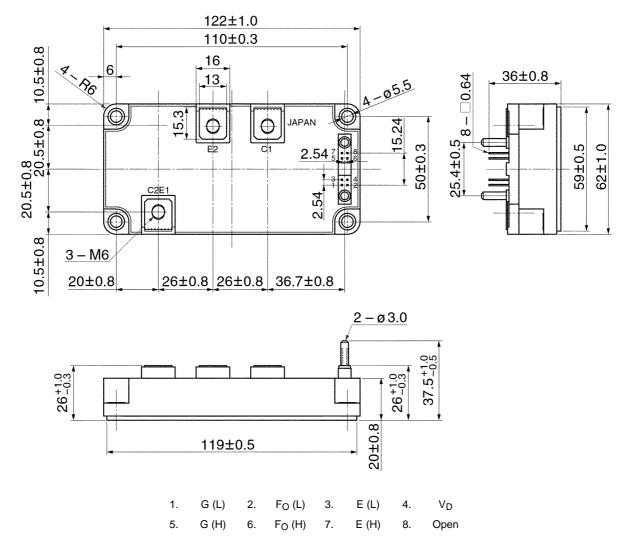
### **Equivalent Circuit**



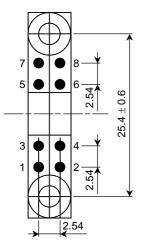
Signa	al terminal						
1.	G (L)	2.	F <sub>O</sub> (L)	3.	E (L)	4.	$V_{D}$
5.	G (H)	6.	F <sub>O</sub> (H)	7.	E (H)	8.	Open

### Package Dimensions: 2-123C1B

Unit: mm



### **Signal Terminal Layout**



4		2		2		4	\/-
1.	G (L)	Ζ.	F <sub>O</sub> (L)	з.	E (L)	4.	۷D
5.	G (H)	6.	F <sub>O</sub> (H)	7.	E (H)	8.	Open

Weight: 375 g

### Maximum Ratings (Ta = 25°C)

Stage	Characteristics		Symbol	Rating	Unit	
	Collector-emitter voltage	V <sub>CES</sub>	600	V		
	Gate-emitter voltage	V <sub>GES</sub>	±20	V		
	Collector current	DC	I <sub>C</sub> 400		٨	
Inverter		1 ms	I <sub>CP</sub>	800	A	
	Forward current	DC	١ <sub>F</sub>	400	А	
	Forward current	1 ms	I <sub>FM</sub>	800	A	
	Collector power dissipation (Tc =	25°C)	P <sub>C</sub>	2160	W	
	Control voltage (OT)	VD	20	V		
Inverter Control Module	Fault input voltage	VFO	20	V		
	Fault input current		IFO	20	mA	
	Junction temperature	Тј	150	°C		
	$\begin{tabular}{ c c c c c c c } \hline Collector power dissipation (Tc = 25°C) & P_C & 2160 \\ \hline Control voltage (OT) & V_D & 20 \\ \hline Fault input voltage & VF_O & 20 \\ \hline Fault input current & IF_O & 20 \\ \hline Fault input current & IF_O & 20 \\ \hline Junction temperature & T_j & 150 \\ \hline Storage temperature range & T_{stg} & -40~125 \\ \hline \end{tabular}$	°C				
Module	Operation temperature range	T <sub>ope</sub>	-20~100	°C		
	Isolation voltage	V <sub>isol</sub>	2500 (AC 1 min)	V		
	Screw torque	—	3 (M5)	N∙m		

# Electrical Characteristics ( $T_j = 25^{\circ}C$ )

### 1. Inverter Stage

Characteristics		Symbol	Test Condition		Min	Тур.	Max	Unit
Gate leakage current			$V_{GE} = \pm 20 \text{ V}, \text{ V}_{CE} = 0$		_		+3/-4	mA
		IGES	$V_{GE} = +10 \text{ V}, \text{ V}_{CE} = 0$				100	nA
Collector cut-off current		ICES	$V_{CE} = 600 \text{ V}, \text{ V}_{GE} = 0$				1.0	mA
Gate-emitter cut-off voltage		V <sub>GE (off)</sub>	$V_{CE} = 5 \text{ V}, \text{ I}_{C} = 400 \text{ mA}$		5.0	6.5	8.0	V
Collector-emitter saturation voltage		V <sub>CE (sat)</sub>	$V_{GE} = 15 V$ ,	Tj = 25°C	_	1.8	2.1	V
				Tj = 125°C	_	_	2.3	v
Input capacitance	)	C <sub>ies</sub>	V <sub>CE</sub> = 10 V, V <sub>GE</sub> = 0, f = 1 MHz		_	3500	_	pF
	Turn-on delay time	t <sub>d (on)</sub>		<sub>CC</sub> = 300 V, I <sub>C</sub> = 400 A <sub>GE</sub> = ±15 V, R <sub>G</sub> = 7.5 Ω (Note 1)	0.10	_	1.00	μs
Switching time	Turn-off time	t <sub>off</sub>			_	_	2.00	
	Fall time	t <sub>f</sub>					0.50	
Reverse recovery time		t <sub>rr</sub>					0.50	
Forward voltage		V <sub>F</sub>	I <sub>F</sub> = 400 A			1.8	2.2	V

Note 1: Switching time test circuit & timing chart

# 2. Control (Tc = 25°C)

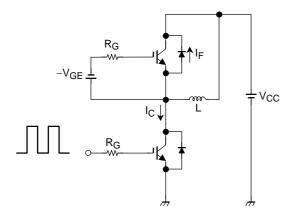
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Fault output current	OC	$V_{GE} = 15 V$	480	_	_	А
Over temperature	OT	—	100	—	125	°C
Fault output delay time	<sup>t</sup> d (Fo)	$V_{CC}=300$ V, $V_{GE}=\pm15$ V	_	—	6.5	μS

# **TOSHIBA**

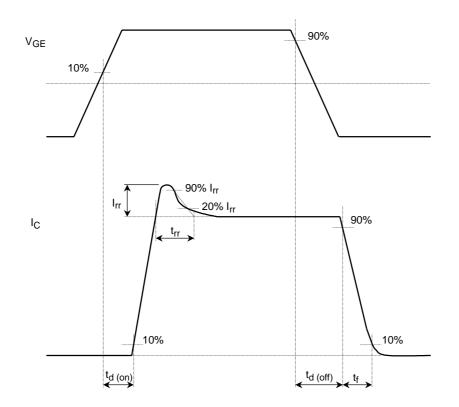
## 3. Module (Tc = $25^{\circ}$ C)

Characteristics Symbol		Test Condition	Min	Тур.	Max	Unit	
Junction to case thermal resistance	Put (1)	Inverter IGBT stage	_	_	0.057 °C/W		
Junction to case thermal resistance	R <sub>th (j-c)</sub>	Inverter FRD stage	_	_	0.068	0/11	
Case to fin thermal resistance	R <sub>th (c-f)</sub>	With silicon compound	_	0.013		°C/W	

# Switching Time Test Circuit



# **Timing Chart**



### Remark

### <Short circuit capability condition>

- Short circuit capability is 6 µs after fault output signal. Please keep following condition to use fault output signal.
  - VCC  $\leq 375$  V
  - $13.8 \text{ V} \le \text{VGE} \le 16.0 \text{ V}$
  - $R_G \ge 7.5 \Omega$
  - $T_j \leq 50^{\circ}C$

### <Gate voltage>

• To use this product, VGE must be provided higher than 13.8 V. In case VGE is less than 13.8 V, fault signal FO may not be output even under error conditions.

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Handbook" etc.,

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